

Search Notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	95	remov\$3 with isolation same ion adj implant\$6 and common adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 06:55
L2	46	remov\$3 with isolation same ion adj implant\$6 and self adj aligned near source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:06
L3	35	remov\$3 with isolation same ion adj implant\$6 and sas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:08
L4	0	sas and sge and anisotropic and ono and "chf.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:09
L5	0	sas and sge and anisotropic and "chf.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:09
L6	2	sas and sge and anisotropic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:11
L7	0	sti and sas and sge and anisotropic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:10
L8	115	sti and sas and anisotropic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:11
L9	0	sti and sas and anisotropic and "chf.su.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:11

L10	15	sti and sas and anisotropic and "chf.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:54
L11	2126	(438/257).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/27 07:55
L12	403	(438/279).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/27 07:55
S1	3032	ion adj implant\$6 and isolation and float\$3 with gate and control with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 20:35
S2	1419	ion adj implant\$6 and isolation and float\$3 with gate and control with gate and ono	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 20:36
S3	494	ion adj implant\$6 and isolation and float\$3 with gate and control with gate and ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:49
S4	343	ion adj implant\$6 and isolation and float\$3 with gate same polysilicon and control with gate and ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:49
S5	283	ion adj implant\$6 and isolation and float\$3 with gate same polysilicon same control with gate and ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:50
S6	154	ion adj implant\$6 and isolation and float\$3 with gate same polysilicon same control with gate same ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/19 15:05
S7	16	ion adj implant\$6 and isolation and float\$3 with gate same polysilicon same control with gate same ono and dry adj etch\$3 and "chf.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:53

S8	9	ion adj implant\$6 and sti and float\$3 with gate same polysilicon same control with gate same ono and dry adj etch\$3 and "chf.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:55
S9	69	ion adj implant\$6 and sti and float\$3 with gate same polysilicon same control with gate same ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 21:55
S10	4	ion adj implant\$6 and isolation and float\$3 with gate same polysilicon same control with gate same ono and dry adj etch\$3 and wash\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/19 15:07
S11	495	ion adj implant\$6 and isolation and float\$3 with gate and control with gate and ono and dry adj etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 05:16
S12	157	remov\$3 with isolation and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 05:30
S13	1131	remov\$3 with isolation same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 06:48
S14	7	remov\$3 near isolation adj layer same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 05:38
S15	8	dong and kwak and ion adj implant\$6 and isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 05:39